

# UNISONIC TECHNOLOGIES CO., LTD

UTT70P10 Preliminary Power MOSFET

# -70A, -100V P-CHANNEL POWER MOSFET

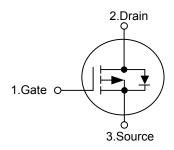
### **■** DESCRIPTION

The UTC **UTT70P10** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance. It can also withstand high energy in the avalanche.

### **■ FEATURES**

- \*  $R_{DS(ON)}$  < 0.03 $\Omega$  @  $V_{GS}$ =-10V,  $I_{D}$ =-20A
- \* High Switching Speed

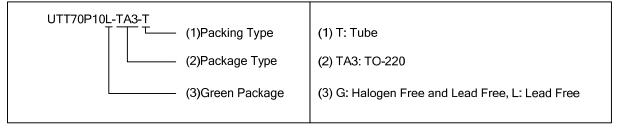
### ■ SYMBOL



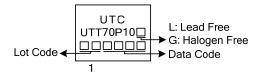
# **■ ORDERING INFORMATION**

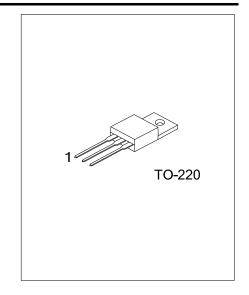
Ordering	Dookogo	Pin Assignment			Dooking		
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTT70P10L-TA3-T	UTT70P10G-TA3-T	TO-220	G	D	S	Tube	

Note: Pin Assignment: G: Gate D: Drain S: Source



## MARKING





<u>www.unisonic.com.tw</u> 1 of 5

# ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>C</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Gate-Source Voltage		$V_{GSS}$	±20	V	
Drain Current	Continuous	I <sub>D</sub>	-70	Α	
	Pulsed	I <sub>DM</sub>	-90	Α	
Power Dissipation		P <sub>D</sub>	225	W	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T <sub>STG</sub>	-55~+150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

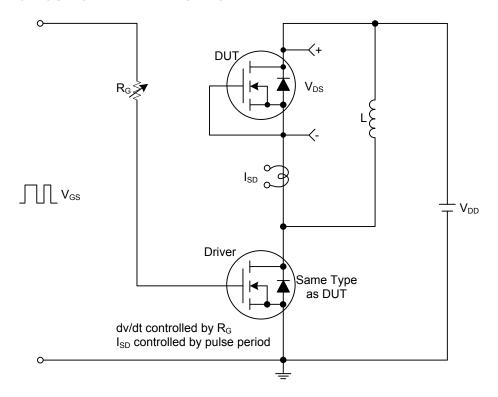
# ■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	$\theta_{JC}$	0.55	°C/W

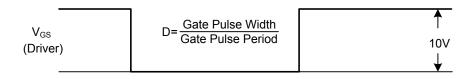
# ■ ELECTRICAL CHARACTERISTICS

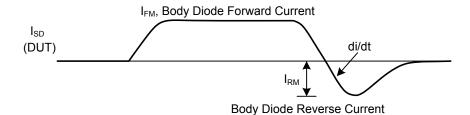
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V				V	
Drain-Source Leakage Current		I <sub>DSS</sub>	V <sub>DS</sub> =0.8×Max.rating,V <sub>GS</sub> =0V,T <sub>J</sub> =25°C			-1	ПΔ	
			$V_{DS}$ =0.8×Max.rating, $V_{GS}$ =0V, $T_J$ =125°C			-500	μA	
Gate- Source Leakage	Forward		V <sub>GS</sub> =+20V			+100	nA	
Current	Reverse	I <sub>GSS</sub>	V <sub>GS</sub> =-20V			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-1		-3	V	
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A			0.03	Ω	
DYNAMIC PARAMETERS	DYNAMIC PARAMETERS							
Input Capacitance		C <sub>ISS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =-50V, f=1.0MHz		2250		pF	
Output Capacitance		Coss			700		pF	
Reverse Transfer Capacitance		C <sub>RSS</sub>			275		pF	
SWITCHING PARAMETERS								
Turn-ON Delay Time		t <sub>D(ON)</sub>	$V_{DD}$ =-50V, $V_{GS}$ =-10V, $I_{D}$ =-50A, $R_{G}$ =1 $\Omega$		20	200	ns	
Rise Time		t <sub>R</sub>			110	420	ns	
Turn-OFF Delay Time		t <sub>D(OFF)</sub>			145	1500	ns	
Fall-Time		t <sub>F</sub>			300	500	ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Drain-Source Diode Forward Voltage		$V_{SD}$	I <sub>F</sub> =-20A, V <sub>GS</sub> =0V, Pulse test, t≤300μs, duty cycle d≤2%		-1.0	-1.5	V	
Body Diode Reverse Recovery Time		t <sub>rr</sub>	T <sub>J</sub> =25°C, I <sub>F</sub> =-20A, V <sub>R</sub> =-50V, di/dt=-100A/µs		80	120	ns	

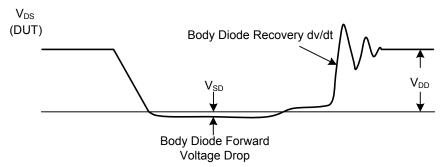
# ■ TEST CIRCUITS AND WAVEFORMS



## Peak Diode Recovery dv/dt Test Circuit



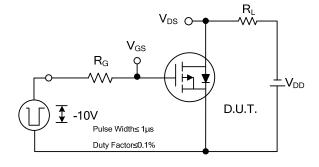


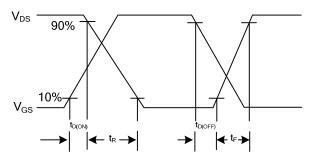


Peak Diode Recovery dv/dt Test Circuit and Waveforms

## Peak Diode Recovery dv/dt Waveforms

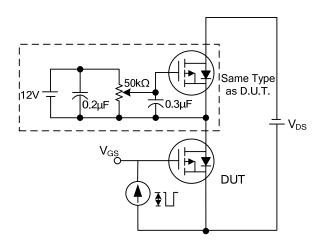
# **■ TEST CIRCUITS AND WAVEFORMS**

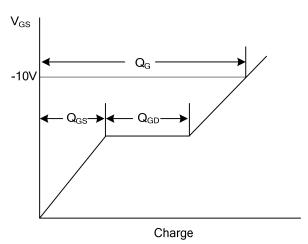




**Switching Test Circuit** 

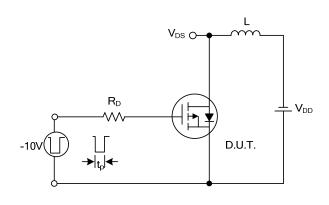
**Switching Waveforms** 

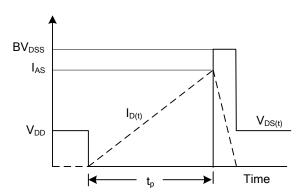




**Gate Charge Test Circuit** 

**Gate Charge Waveform** 





**Unclamped Inductive Switching Test Circuit** 

**Unclamped Inductive Switching Waveforms** 

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

